

Quad 2-Channel Multiplexer

MC74VHC157, MC74VHCT157A

The MC74VHC157/MC74VHCT157A is an advanced high speed CMOS quad 2-channel multiplexer fabricated with silicon gate CMOS technology. It achieves high speed operation similar to equivalent Bipolar Schottky TTL while maintaining CMOS low power dissipation.

It consists of four 2-input digital multiplexers with common select (S) and enable ($\bar{E}$) inputs. When $\bar{E}$ is held High, selection of data is inhibited and all the outputs go Low.

The select decoding determines whether the A or B inputs get routed to the corresponding Y outputs.

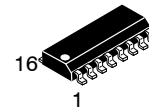
The MC74VHC157 inputs are compatible with standard CMOS levels while the MC74VHCT157A inputs are compatible with TTL levels. The MC74VHCT157A can be used as a level converter for interfacing 3.3 V to 5.0 V, because it has full 5.0 V CMOS level output swings.

The internal circuit is composed of three stages, including a buffer output which provides high noise immunity and stable output. The MC74VHC157 and MC74VHCT157A input structures tolerate voltages up to 5.5 V, allowing the interface of 5 V systems to 3 V systems.

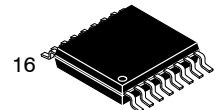
The MC74VHCT157A output structures provide protection when $V_{CC} = 0$ V. These output structures help prevent device destruction caused by supply voltage – input/output voltage mismatch, battery backup, hot insertion, etc.

Features

- High Speed: $t_{PD} = 4.1$ ns (Typ) at $V_{CC} = 5.0$ V
- Low Power Dissipation: $I_{CC} = 4.0$ μ A (Max) at $T_A = 25^\circ\text{C}$
- High Noise Immunity: $V_{NIH} = V_{NIL} = 28\%$
- Power Down Protection Provided
- Balanced Propagation Delays
- Designed for 2.0 V to 5.5 V (VHC)
4.5 V to 5.5 V (VHCT)
- Low Noise: $V_{OLP} = 0.8$ V (Max)
- Pin and Function Compatible with Other Standard Logic Families
- Latchup Performance Exceeds 100 mA
- ESD Performance: Human Body Model > 2000 V
- Chip Complexity: 82 FETs or 20 Equivalent Gates
- –Q Suffix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q100 Qualified and PPAP Capable
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS-Compliant



SOIC-16
D SUFFIX
CASE 751B

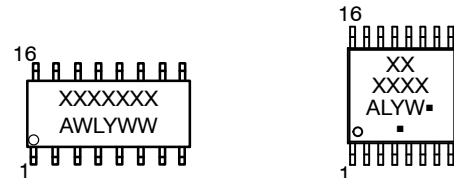


TSSOP-16
DT SUFFIX
CASE 948F



QFN16
MN SUFFIX
CASE 485AW

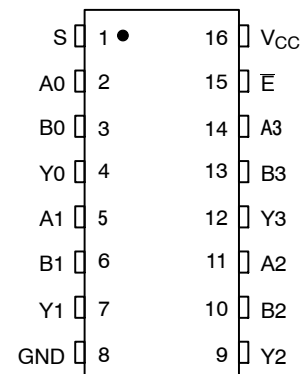
MARKING DIAGRAMS



- A = Assembly Location
 WL, L = Wafer Lot
 YY, Y = Year
 WW, W = Work Week
 G or $\blacksquare$ = Pb-Free Package

(Note: Microdot may be in either location)

PIN ASSIGNMENTS



FUNCTION TABLE

Inputs		Outputs
$\bar{E}$	S	Y0 – Y3
H	X	L
L	L	A0 – A3
L	H	B0 – B3

A0 – A3, B0 – B3 = the levels of the respective Data-Word Inputs.

ORDERING INFORMATION

See detailed ordering and shipping information on page 8 of this data sheet.

MC74VHC157, MC74VHCT157A

MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V_{CC}	DC Supply Voltage	−0.5 to +6.5	V
V_{IN}	DC Input Voltage	−0.5 to +6.5	V
V_{OUT}	DC Output Voltage (MC74VHC)	−0.5 to $V_{CC} + 0.5$	V
	DC Output Voltage (MC74VHCT) Active Mode (High or Low State) Tristate Mode (Note 1) Power-Off Mode ($V_{CC} = 0$ V)	−0.5 to $V_{CC} + 0.5$ −0.5 to +6.5 −0.5 to +6.5	
I_{IN}	DC Input Current, per Pin	±20	mA
I_{OUT}	DC Output Current, per Pin	±25	mA
I_{CC}	DC Supply Current, V_{CC} and GND Pins	±100	mA
I_{IK}	Input Clamp Current	−20	mA
I_{OK}	Output Clamp Current MC74VHC MC74VHCT	±20 −20	mA
T_{STG}	Storage Temperature Range	−65 to +150	°C
T_L	Lead Temperature, 1 mm from Case for 10 secs	260	°C
T_J	Junction Temperature Under Bias	+150	°C
θ_{JA}	Thermal Resistance (Note 2) SOIC-16 QFN16 TSSOP-16	126 118 159	°C/W
P_D	Power Dissipation in Still Air at 25°C SOIC-16 QFN16 TSSOP-16	995 1062 787	mW
MSL	Moisture Sensitivity	Level 1	–
F_R	Flammability Rating Oxygen Index: 28 to 34	UL 94 V-0 @ 0.157 in	–
V_{ESD}	ESD Withstand Voltage (Note 3) Human Body Model Charged Device Model	>2000 N/A	V
$I_{LATCHUP}$	Latchup Performance (Note 4)	±100	mA

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. Applicable to devices with outputs that may be tri-stated.
2. Measured with minimum pad spacing on an FR4 board, using 76 mm-by-114 mm, 2-ounce copper trace no air flow per JESD51-7.
3. HBM tested to EIA / JESD22-A114-A. CDM tested to JESD22-C101-A. JEDEC recommends that ESD qualification to EIA/JESD22-A115A (Machine Model) be discontinued.
4. Tested to EIA/JESD78 Class II.

MC74VHC157, MC74VHCT157A

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Min	Max	Unit
MC74VHC				
V_{CC}	DC Supply Voltage	2.0	5.5	V
V_{IN}	DC Input Voltage (Note 5)	0	5.5	V
V_{OUT}	DC Output Voltage (Note 5)	0	V_{CC}	V
T_A	Operating Temperature	-55	+125	°C
t_r, t_f	Input Rise or Fall Rate	$V_{CC} = 3.0\text{ V to }3.6\text{ V}$ $V_{CC} = 4.5\text{ V to }5.5\text{ V}$		ns/V
		0	100	
		0	20	

MC74VHCT

V_{CC}	DC Supply Voltage	4.5	5.5	V
V_{IN}	DC Input Voltage (Note 5)	0	5.5	V
V_{OUT}	DC Output Voltage (Note 5)	Active Mode (High or Low State) Tristate Mode Power-Off Mode ($V_{CC} = 0\text{ V}$)		V
		0	V_{CC}	
		0	5.5	
		0	5.5	
T_A	Operating Temperature	-55	+125	°C
t_r, t_f	Input Rise or Fall Rate	$V_{CC} = 4.5\text{ V to }5.5\text{ V}$		ns/V
		0	20	

Functional operation above the stresses listed in the Recommended Operating Ranges is not implied. Extended exposure to stresses beyond the Recommended Operating Ranges limits may affect device reliability.

5. Unused inputs must always be tied to an appropriate logic voltage level (e.g., either GND or V_{CC}). Unused outputs must be left open.

MC74VHC157, MC74VHCT157A

DC CHARACTERISTICS (MC74VHC157)

Symbol	Parameter	Condition	V _{CC} (V)	T _A = 25°C			T _A ≤ 85°C		-55°C ≤ T _A ≤ 125°C		Unit
				Min	Typ	Max	Min	Max	Min	Max	
V _{IH}	High-Level Input Voltage		2.0 3.0 to 5.5	1.5 0.7 V _{CC}			1.5 0.7 V _{CC}		1.5 0.7 V _{CC}		V
V _{IL}	Low-Level Input Voltage		2.0 3.0 to 5.5			0.5 0.3 V _{CC}		0.5 0.3 V _{CC}		0.5 0.3 V _{CC}	V
V _{OH}	High-Level Output Voltage	V _{IN} = V _{IH} or V _{IL} I _{OH} = -50 µA	2.0 3.0 4.5	1.9 2.9 4.4	2.0 3.0 4.5		1.9 2.9 4.4		1.9 2.9 4.4		V
		V _{IN} = V _{IH} or V _{IL} I _{OH} = -4 mA I _{OH} = -8 mA	3.0 4.5	2.58 3.94			2.48 3.8		2.34 3.66		
V _{OL}	Low-Level Output Voltage	V _{IN} = V _{IH} or V _{IL} I _{OL} = 50 µA	2.0 3.0 4.5		0.0 0.0 0.0	0.1 0.1 0.1		0.1 0.1 0.1		0.1 0.1 0.1	V
		V _{IN} = V _{IH} or V _{IL} I _{OH} = 4 mA I _{OH} = 8 mA	3.0 4.5			0.36 0.36		0.44 0.44		0.52 0.52	
I _{IN}	Input Leakage Current	V _{IN} = 5.5 V or GND	0 to 5.5			± 0.1		± 1.0		± 1.0	µA
I _{CC}	Quiescent Supply Current	V _{IN} = V _{CC} or GND	5.5			4.0		40.0		40.0	µA

AC ELECTRICAL CHARACTERISTICS (MC74VHC157)

Symbol	Characteristic	Test Conditions	T _A = 25°C			T _A ≤ 85°C		-55°C ≤ T _A ≤ 125°C		Unit
			Min	Typ	Max	Typ	Max	Typ	Max	
t _{PLH} , t _{PHL}	Propagation Delay, A to B to Y	V _{CC} = 3.3 ± 0.3 V C _L = 15 pF C _L = 50 pF		6.2 8.7	9.7 13.2	1.0 1.0	11.5 15.0	1.0 1.0	11.5 15.0	ns
		V _{CC} = 5.0 ± 0.5 V C _L = 15 pF C _L = 50 pF		4.1 5.6	6.4 8.4	1.0 1.0	7.5 9.5	1.0 1.0	7.5 9.5	
t _{PLH} , t _{PHL}	Propagation Delay, S to Y	V _{CC} = 3.3 ± 0.3 V C _L = 15 pF C _L = 50 pF		8.4 10.9	13.2 16.7	1.0 1.0	15.5 19.0	1.0 1.0	15.5 19.0	ns
		V _{CC} = 5.0 ± 0.5 V C _L = 15 pF C _L = 50 pF		5.3 6.8	8.1 10.1	1.0 1.0	9.5 11.5	1.0 1.0	9.5 11.5	
t _{PLH} , t _{PHL}	Propagation Delay, E to Y	V _{CC} = 3.3 ± 0.3 V C _L = 15 pF C _L = 50 pF		8.7 11.2	13.6 17.1	1.0 1.0	16.0 19.5	1.0 1.0	16.0 19.5	ns
		V _{CC} = 5.0 ± 0.5 V C _L = 15 pF C _L = 50 pF		5.6 7.1	8.6 10.6	1.0 1.0	10.0 12.0	1.0 1.0	10.0 12.0	
C _{IN}	Input Capacitance			4	10		10		10	pF

C _{PD}	Power Dissipation Capacitance (Note 6)	Typical @ 25°C, V _{CC} = 5.0 V	pF
		20	

6. C_{PD} is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load. Average operating current can be obtained by the equation: I_{CC(OPR)} = C_{PD} • V_{CC} • f_{in} + I_{CC}. C_{PD} is used to determine the no-load dynamic power consumption: P_D = C_{PD} • V_{CC}² • f_{in} + I_{CC} • V_{CC}.

NOISE CHARACTERISTICS (MC74VHC157; C_L = 50 pF; V_{CC} = 5.0 V)

Symbol	Characteristic	T _A = 25°C		Unit
		Typ	Max	
V _{OLP}	Quiet Output Maximum Dynamic V _{OL}	0.3	0.8	V
V _{OLV}	Quiet Output Minimum Dynamic V _{OL}	-0.3	-0.8	V
V _{IHD}	Minimum High Level Dynamic Input Voltage		3.5	V
V _{ILD}	Maximum Low Level Dynamic Input Voltage		1.5	V

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DC CHARACTERISTICS (MC74VHCT157A)

Symbol	Parameter	Condition	V _{CC} (V)	T _A = 25°C			T _A ≤ 85°C		-55°C ≤ T _A ≤ 125°C		Unit
				Min	Typ	Max	Min	Max	Min	Max	
V _{IH}	Minimum High-Level Input Voltage		4.5 to 5.5	2			2	0.8	2		V
V _{IL}	Maximum Low-Level Input Voltage		4.5 to 5.5			0.8		0.8		0.8	V
V _{OH}	Maximum High-Level Output Voltage	V _{IN} = V _{IH} or V _{IL} I _{OH} = -50 μA	4.5	4.4	4.5		4.4		4.4		V
		V _{IN} = V _{IH} or V _{IL} I _{OH} = -8 mA	4.5	3.94			3.8		3.66		
V _{OL}	Maximum Low-Level Output Voltage	V _{IN} = V _{IH} or V _{IL} I _{OL} = 50 μA	4.5		0.0	0.1		0.1		0.1	V
		V _{IN} = V _{IH} or V _{IL} I _{OH} = 8 mA	4.5			0.36		0.44		0.52	
I _{IN}	Input Leakage Current	V _{IN} = 5.5 V or GND	0 to 5.5			±0.1		±1.0		±1.0	μA
I _{CC}	Maximum Quiescent Supply Current	V _{IN} = V _{CC} or GND	5.5			4.0		40.0		40.0	μA
I _{CCT}	Additional Quiescent Supply Current (per Pin)	Any one input: V _{IN} = 3.4 V All other inputs: V _{IN} = V _{CC} or GND	5.5			1.35		1.5		1.5	μA
I _{OPD}	Output Leakage Current	V _{OUT} = 5.5 V	0			0.5		5		5	μA

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

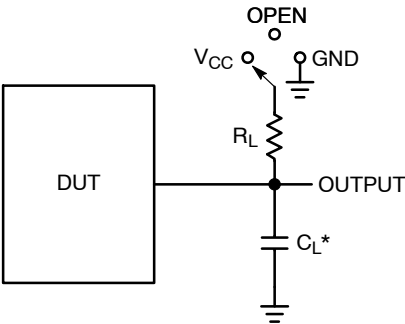
AC ELECTRICAL CHARACTERISTICS (MC74VHCT157A)

Symbol	Parameter	Test Conditions	T _A = 25°C			T _A ≤ 85°C		-55°C ≤ T _A ≤ 125°C		Unit
			Min	Typ	Max	Min	Max	Min	Max	
t _{PLH} , t _{PHL}	Maximum Propagation Delay; A to B to Y	V _{CC} = 3.3 ± 0.3 V C _L = 15pF C _L = 50pF		5.6 8.0	7.0 10.0	1.0 1.0	7.7 11.0	1.0 1.0	7.7 11.0	ns
		V _{CC} = 5.0 ± 0.5 V C _L = 15pF C _L = 50pF		4.1 5.6	6.4 8.4	1.0 1.0	7.5 9.5	1.0 1.0	7.5 9.5	
t _{PLH} , t _{PHL}	Maximum Propagation Delay; S to Y	V _{CC} = 3.3 ± 0.3 V C _L = 15pF C _L = 50pF		6.1 8.5	7.5 10.5	1.0 1.0	8.2 11.5	1.0 1.0	8.2 11.5	ns
		V _{CC} = 5.0 ± 0.5 V C _L = 15pF C _L = 50pF		5.3 6.8	8.1 10.1	1.0 1.0	9.5 11.5	1.0 1.0	9.5 11.5	
t _{PLH} , t _{PHL}	Maximum Propagation Delay; E to Y	V _{CC} = 3.3 ± 0.3 V C _L = 15pF C _L = 50pF		6.1 8.5	7.5 10.5	1.0 1.0	8.2 11.5	1.0 1.0	8.2 11.5	ns
		V _{CC} = 5.0 ± 0.5 V C _L = 15pF C _L = 50pF		5.6 7.1	8.6 10.6	1.0 1.0	10.0 12.0	1.0 1.0	10.0 12.0	
C _{IN}	Maximum Input Capacitance			4	10		10		10	pF

C _{PD}	Power Dissipation Capacitance (Note 7)	Typical @ 25°C, V _{CC} = 5.0 V	pF
		20	

7. C_{PD} is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load. Average operating current can be obtained by the equation: I_{CC(OPR)} = C_{PD} • V_{CC} • f_{in} + I_{CC}. C_{PD} is used to determine the no-load dynamic power consumption; P_D = C_{PD} • V_{CC}² • f_{in} + I_{CC} • V_{CC}.

MC74VHC157, MC74VHCT157A



*C_L Includes probe and jig capacitance

Test	Switch Position	C _L	R _L
t _{PLH} / t _{PHL}	Open	See AC Characteristics Table	1 kΩ
t _{PLZ} / t _{PZL}	V _{CC}		
t _{PHZ} / t _{PZH}	GND		

Figure 1. Test Circuit

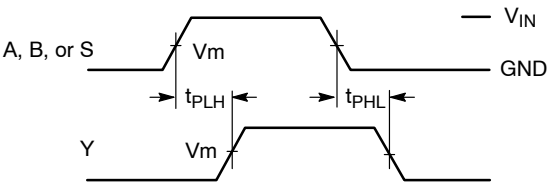


Figure 2. Switching Waveform

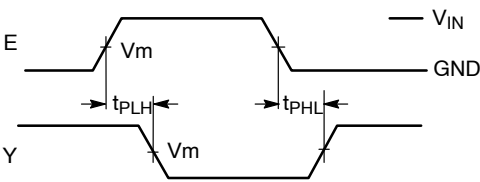


Figure 3. Inverting Switching

Device	V _{IN} , V	V _m , V
MC74VHC157	V _{CC}	50% x V _{CC}
MC74VHCT157A	3 V	1.5 V

MC74VHC157, MC74VHCT157A

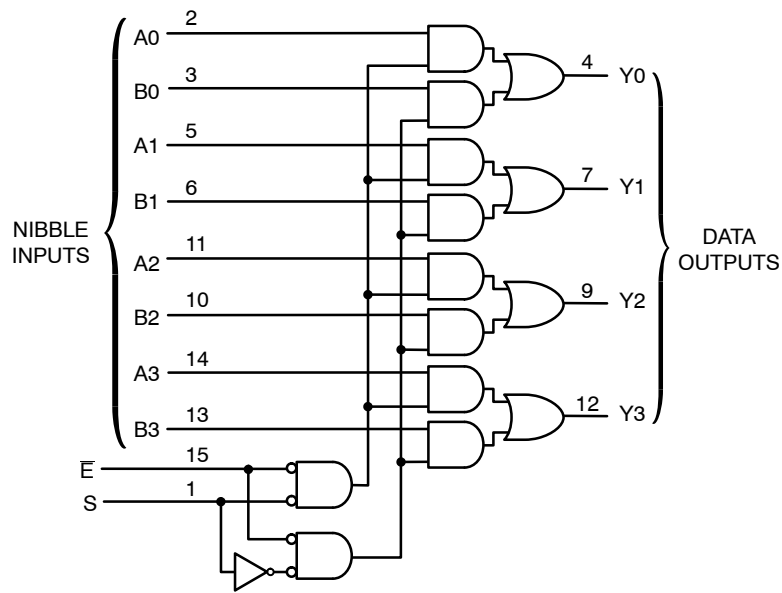


Figure 4. Expanded Logic Diagram

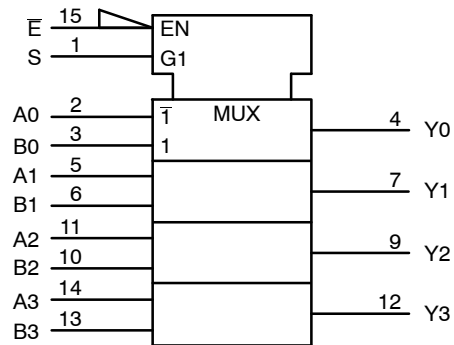


Figure 5. IEC Logic Symbol

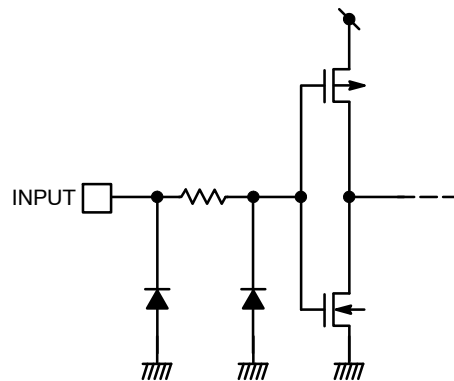


Figure 6. Input Equivalent Circuit

MC74VHC157, MC74VHCT157A

ORDERING INFORMATION

Device	Marking	Package	Shipping†
MC74VHC157DR2G	VHC157G	SOIC-16	2500 / Tape & Reel
MC74VHC157DTR2G	VHC 157	TSSOP-16	2500 / Tape & Reel
MC74VHC157DTR2G-Q*	VHC 157	TSSOP-16	2500 / Tape & Reel
MC74VHCT157ADTR2G	VHCT 157A	TSSOP-16	2500 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

*-Q Suffix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q100 Qualified and PPAP Capable.

MC74VHC157, MC74VHCT157A

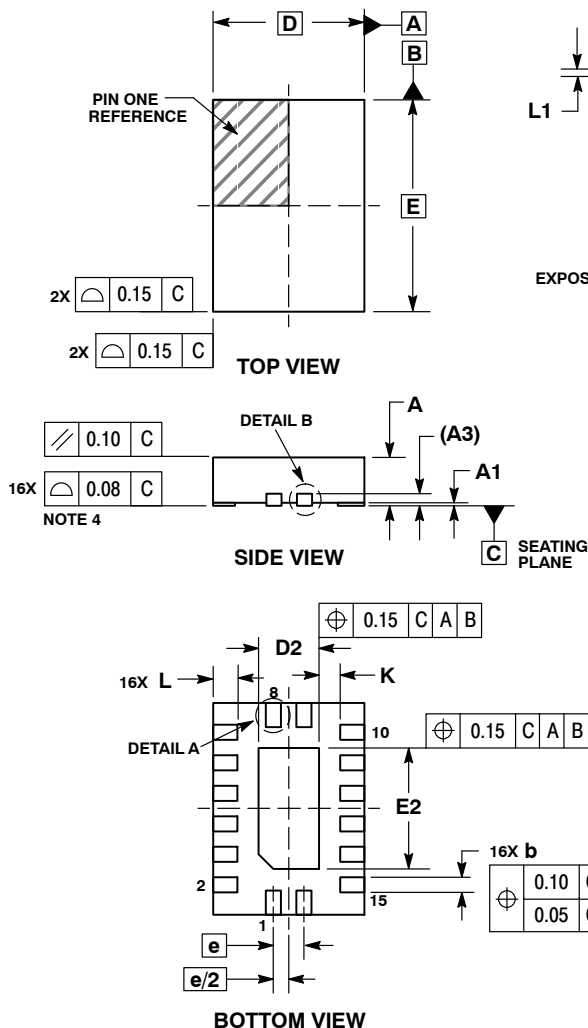
PACKAGE DIMENSIONS



SCALE 2:1

QFN16, 2.5x3.5, 0.5P
CASE 485AW
ISSUE O

DATE 11 DEC 2008

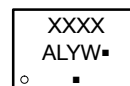


NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. DIMENSIONS b APPLIES TO PLATED TERMINAL AND IS MEASURED BETWEEN 0.15 AND 0.30 MM FROM TERMINAL.
4. COPLANARITY APPLIES TO THE EXPOSED PAD AS WELL AS THE TERMINALS.

MILLIMETERS		
DIM	MIN	MAX
A	0.80	1.00
A1	0.00	0.05
A3	0.20	REF
b	0.20	0.30
D	2.50	BSC
D2	0.85	1.15
E	3.50	BSC
E2	1.85	2.15
e	0.50	BSC
K	0.20	---
L	0.35	0.45
L1	---	0.15

GENERIC MARKING DIAGRAM*

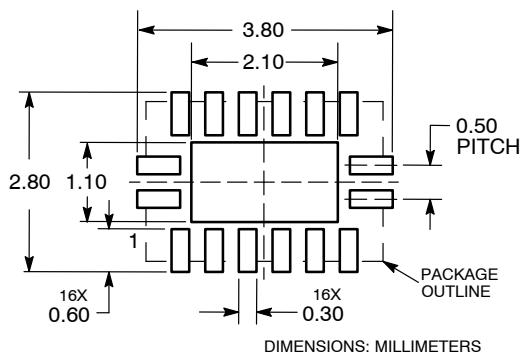


- XXXX = Specific Device Code
A = Assembly Location
L = Wafer Lot
Y = Year
W = Work Week
▪ = Pb-Free Package

(Note: Microdot may be in either location)

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "▪", may or may not be present. Some products may not follow the Generic Marking.

RECOMMENDED SOLDERING FOOTPRINT*



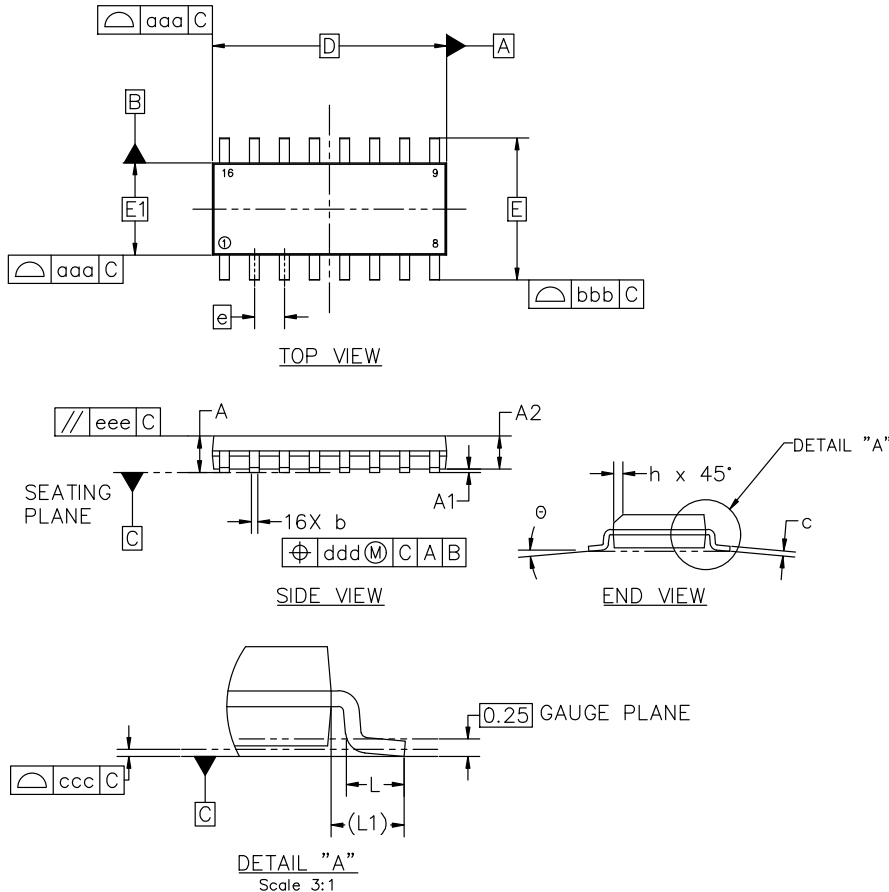
*For additional information on our Pb-Free strategy and soldering details, please download the **onsemi** Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.


SOIC-16 9.90x3.90x1.37 1.27P
CASE 751B
ISSUE M

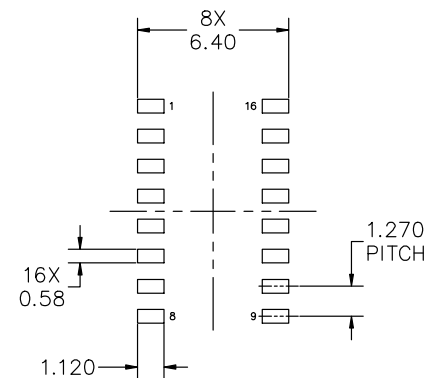
DATE 18 OCT 2024

NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 2018.
2. DIMENSION IN MILLIMETERS. ANGLE IN DEGREES.
3. DIMENSIONS D AND E1 DO NOT INCLUDE MOLD PROTRUSION.
4. MAXIMUM MOLD PROTRUSION 0.15mm PER SIDE.
5. DIMENSION b DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.127mm TOTAL IN EXCESS OF THE b DIMENSION AT MAXIMUM MATERIAL CONDITION.



MILLIMETERS			
DIM	MIN	NOM	MAX
A	1.35	1.55	1.75
A1	0.10	0.18	0.25
A2	1.25	1.37	1.50
b	0.35	0.42	0.49
c	0.19	0.22	0.25
D	9.90 BSC		
E	6.00 BSC		
E1	3.90 BSC		
e	1.27 BSC		
h	0.25	---	0.50
L	0.40	0.83	1.25
L1	1.05 REF		
θ	0°	---	7°
TOLERANCE OF FORM AND POSITION			
aaa	0.10		
bbb	0.20		
ccc	0.10		
ddd	0.25		
eee	0.10		



*FOR ADDITIONAL INFORMATION ON OUR
PB-FREE STRATEGY AND SOLDERING DETAILS,
PLEASE DOWNLOAD THE onsemi SOLDERING
AND MOUNTING TECHNIQUES REFERENCE
MANUAL, SOLDERM/D

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SOIC-16 9.90x3.90x1.37 1.27P
CASE 751B
ISSUE M

DATE 18 OCT 2024

GENERIC
MARKING DIAGRAM*



XXXXX = Specific Device Code
A = Assembly Location
WL = Wafer Lot
Y = Year
WW = Work Week
G = Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "▪", may or may not be present. Some products may not follow the Generic Marking.

STYLE 1: PIN 1. COLLECTOR 2. BASE 3. EMITTER 4. NO CONNECTION 5. EMITTER 6. BASE 7. COLLECTOR 8. COLLECTOR 9. BASE 10. EMITTER 11. NO CONNECTION 12. EMITTER 13. BASE 14. COLLECTOR 15. EMITTER 16. COLLECTOR	STYLE 2: PIN 1. CATHODE 2. ANODE 3. NO CONNECTION 4. CATHODE 5. CATHODE 6. NO CONNECTION 7. ANODE 8. CATHODE 9. CATHODE 10. ANODE 11. NO CONNECTION 12. CATHODE 13. CATHODE 14. NO CONNECTION 15. ANODE 16. CATHODE	STYLE 3: PIN 1. COLLECTOR, DYE #1 2. BASE, #1 3. EMITTER, #1 4. COLLECTOR, #1 5. COLLECTOR, #2 6. BASE, #2 7. EMITTER, #2 8. COLLECTOR, #2 9. COLLECTOR, #3 10. BASE, #3 11. EMITTER, #3 12. COLLECTOR, #3 13. COLLECTOR, #4 14. BASE, #4 15. EMITTER, #4 16. COLLECTOR, #4	STYLE 4: PIN 1. COLLECTOR, DYE #1 2. COLLECTOR, #1 3. COLLECTOR, #2 4. COLLECTOR, #2 5. COLLECTOR, #3 6. COLLECTOR, #3 7. COLLECTOR, #4 8. COLLECTOR, #4 9. BASE, #4 10. EMITTER, #4 11. BASE, #3 12. EMITTER, #3 13. BASE, #2 14. EMITTER, #2 15. BASE, #1 16. EMITTER, #1
STYLE 5: PIN 1. DRAIN, DYE #1 2. DRAIN, #1 3. DRAIN, #2 4. DRAIN, #2 5. DRAIN, #3 6. DRAIN, #3 7. DRAIN, #4 8. DRAIN, #4 9. GATE, #4 10. SOURCE, #4 11. GATE, #3 12. SOURCE, #3 13. GATE, #2 14. SOURCE, #2 15. GATE, #1 16. SOURCE, #1	STYLE 6: PIN 1. CATHODE 2. CATHODE 3. CATHODE 4. CATHODE 5. CATHODE 6. CATHODE 7. CATHODE 8. CATHODE 9. ANODE 10. ANODE 11. ANODE 12. ANODE 13. ANODE 14. ANODE 15. ANODE 16. ANODE	STYLE 7: PIN 1. SOURCE N-CH 2. COMMON DRAIN (OUTPUT) 3. COMMON DRAIN (OUTPUT) 4. GATE P-CH 5. COMMON DRAIN (OUTPUT) 6. COMMON DRAIN (OUTPUT) 7. COMMON DRAIN (OUTPUT) 8. SOURCE P-CH 9. SOURCE P-CH 10. COMMON DRAIN (OUTPUT) 11. COMMON DRAIN (OUTPUT) 12. COMMON DRAIN (OUTPUT) 13. GATE N-CH 14. COMMON DRAIN (OUTPUT) 15. COMMON DRAIN (OUTPUT) 16. SOURCE N-CH	

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TSSOP-16 WB
CASE 948F
ISSUE B

DATE 19 OCT 2006


NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETER.
3. DIMENSION A DOES NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS. MOLD FLASH OR GATE BURRS SHALL NOT EXCEED 0.15 (0.006) PER SIDE.
4. DIMENSION B DOES NOT INCLUDE INTERLEAD FLASH OR PROTRUSION. INTERLEAD FLASH OR PROTRUSION SHALL NOT EXCEED 0.25 (0.010) PER SIDE.
5. DIMENSION K DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE K DIMENSION AT MAXIMUM MATERIAL CONDITION.
6. TERMINAL NUMBERS ARE SHOWN FOR REFERENCE ONLY.
7. DIMENSION A AND B ARE TO BE DETERMINED AT DATUM PLANE -W-.

DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	4.90	5.10	0.193	0.200
B	4.30	4.50	0.169	0.177
C	---	1.20	---	0.047
D	0.05	0.15	0.002	0.006
F	0.50	0.75	0.020	0.030
G	0.65 BSC		0.026 BSC	
H	0.18	0.28	0.007	0.011
J	0.09	0.20	0.004	0.008
J1	0.09	0.16	0.004	0.006
K	0.19	0.30	0.007	0.012
K1	0.19	0.25	0.007	0.010
L	6.40 BSC		0.252 BSC	
M	0°	8°	0°	8°

**RECOMMENDED
SOLDERING FOOTPRINT***


*For additional information on our Pb-Free strategy and soldering details, please download the onsemi Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

**GENERIC
MARKING DIAGRAM***


XXXX = Specific Device Code
A = Assembly Location
L = Wafer Lot
Y = Year
W = Work Week
G or ■ = Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "■", may or may not be present. Some products may not follow the Generic Marking.

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